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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

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Team Nexperia

PDTA114E series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

Rev. 10 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package	Package		NPN	Package	
	NXP JEITA JEDEC complement	configuration				
PDTA114EE	SOT416	SC-75	-	PDTC114EE	ultra small	
PDTA114EM	SOT883	SC-101	-	PDTC114EM	leadless ultra small	
PDTA114ET	SOT23	-	TO-236AB	PDTC114ET	small	
PDTA114EU	SOT323	SC-70	-	PDTC114EU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		8.0	1.0	1.2	



2. Pinning information

Table 3. **Pinning** Pin Simplified outline **Graphic symbol** Description SOT23; SOT323; SOT416 1 input (base) 3 2 GND (emitter) 3 output (collector) 2 006aaa144 sym003 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent top view

3. Ordering information

Table 4. Ordering information

Type number	Package	Package						
	Name	Description	Version					
PDTA114EE	SC-75	plastic surface-mounted package; 3 leads	SOT416					
PDTA114EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883					
PDTA114ET	-	plastic surface-mounted package; 3 leads	SOT23					
PDTA114EU	SC-70	plastic surface-mounted package; 3 leads	SOT323					

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTA114EE	03
PDTA114EM	E5
PDTA114ET	*03
PDTA114EU	*03

^{[1] * =} placeholder for manufacturing site code.

5. Limiting values

Table 6. Limiting values

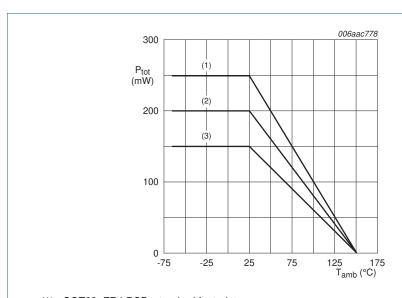
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-10	V
I _O	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTA114EE (SOT416)		[1][2] -	150	mW
	PDTA114EM (SOT883)		[2][3]	250	mW
	PDTA114ET (SOT23)		[1] -	250	mW
	PDTA114EU (SOT323)		[1] -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

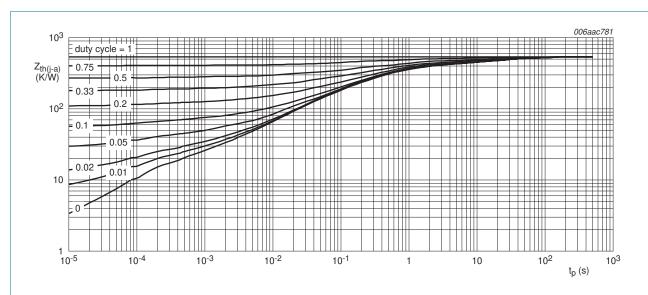
Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

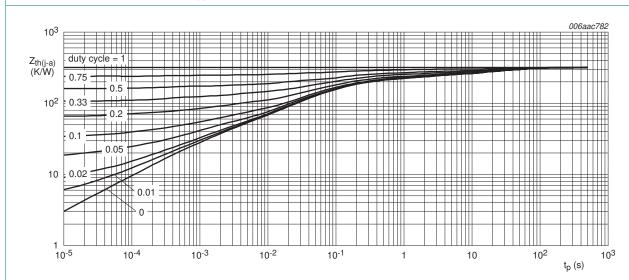
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTA114EE (SOT416)		[1][2]	-	830	K/W
	PDTA114EM (SOT883)		[2][3]	-	500	K/W
	PDTA114ET (SOT23)		[1] -	-	500	K/W
	PDTA114EU (SOT323)		[1] -	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114EE (SOT416); typical values



FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114EM (SOT883); typical values

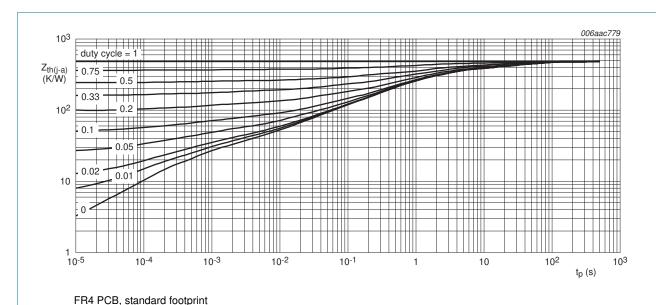


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for

FR4 PCB, standard footprint

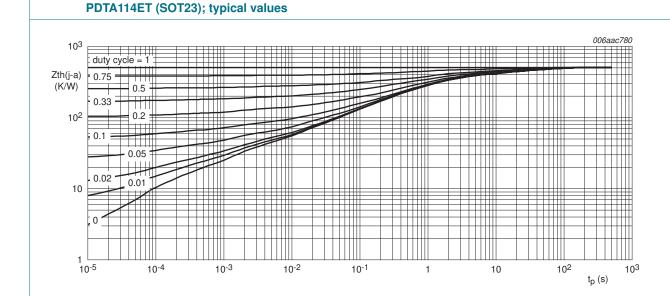


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114EU (SOT323); typical values

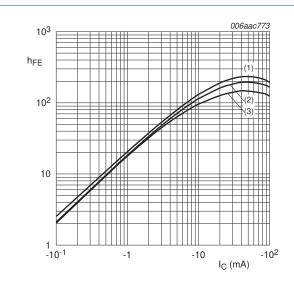
7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Parameter					
Faiailietei	Conditions	Min	Тур	Max	Unit
collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
collector-emitter	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μА
cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	- 5	μΑ
emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-400	μΑ
DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	30	-	-	
collector-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	-	-	-150	mV
off-state input voltage	$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A}$	-	-1.1	-0.8	V
on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_{C} = -10 \text{ mA}$	-2.5	-1.8	-	V
bias resistor 1 (input)		7	10	13	kΩ
bias resistor ratio		8.0	1.0	1.2	
collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	-	-	3	pF
transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ f = 100 MHz	[1] -	180	-	MHz
	cut-off current collector-emitter cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage off-state input voltage on-state input voltage bias resistor 1 (input) bias resistor ratio collector capacitance	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \text{cut-off current} \\ \text{collector-emitter} \\ \text{cut-off current} \\ \end{array} \begin{array}{c} V_{CE} = -30 \text{ V}; \ I_B = 0 \text{ A} \\ V_{CE} = -30 \text{ V}; \ I_B = 0 \text{ A}; \\ T_j = 150 \text{ °C} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array} \\ \end{array} \begin{array}{c} - $	

^[1] Characteristics of built-in transistor.



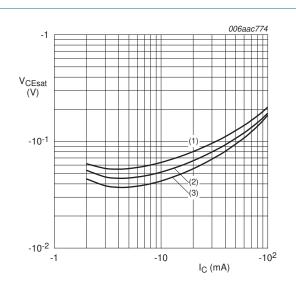
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values



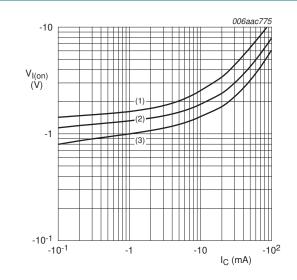
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



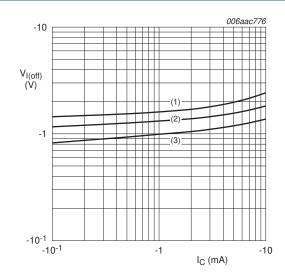
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Off-state input voltage as a function of collector current; typical values

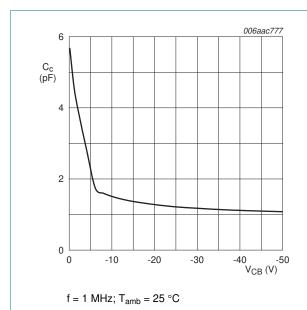


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

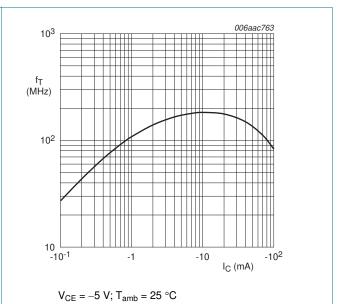


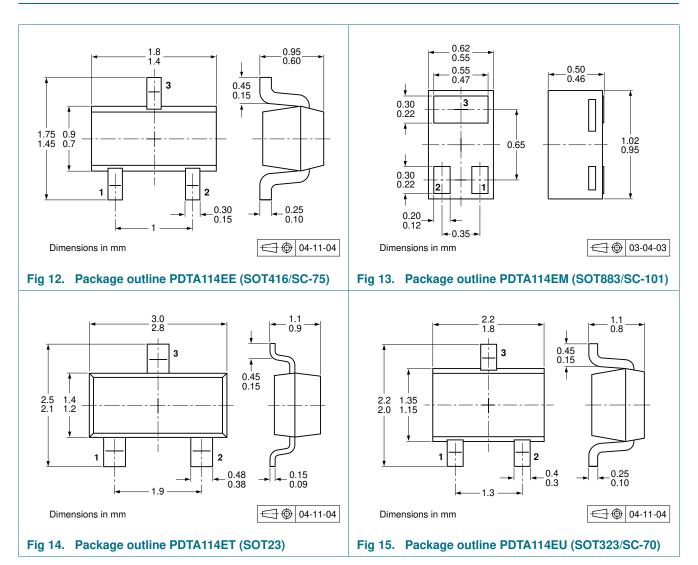
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

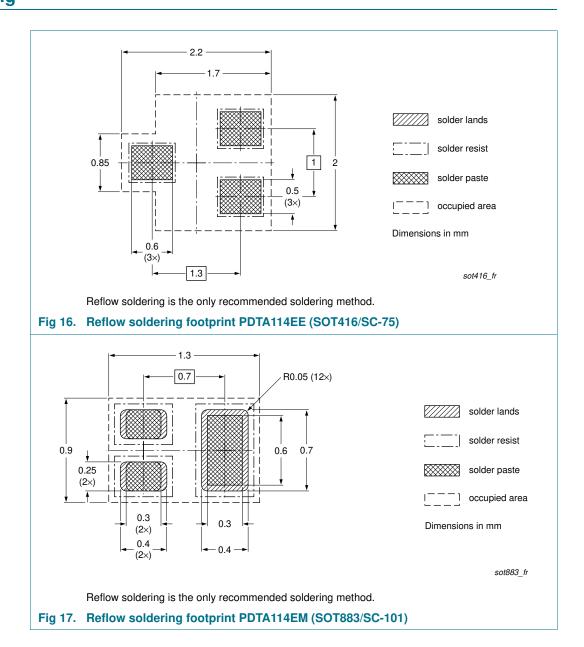
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

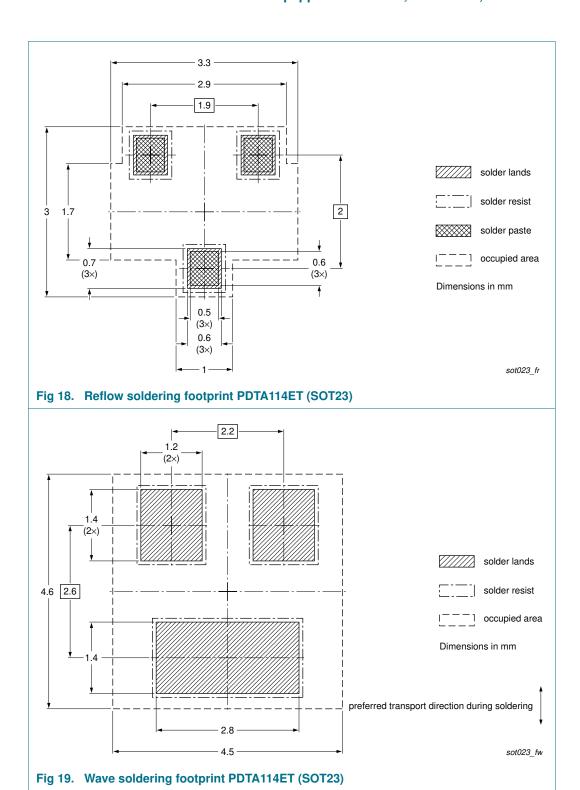
Type number	Package	Description	Packing	Packing quantity		
			3000	10000		
PDTA114EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135		
PDTA114EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-315		
PDTA114ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
PDTA114EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135		

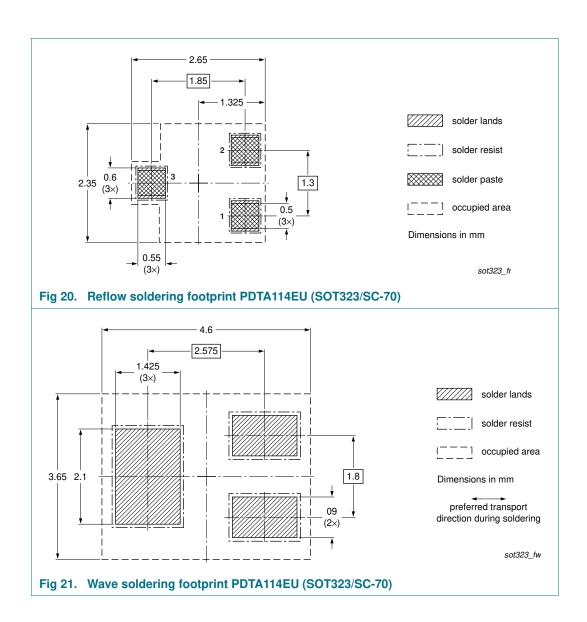
^[1] For further information and the availability of packing methods, see $\underline{\text{Section 14}}$.

PDTA114E_SER

11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA114E_SER v.10	20111221	Product data sheet	-	PDTA114E_SER v.9
Modifications:	• Figure 2 and	5: corrected		
PDTA114E_SER v.9	20111122	Product data sheet	-	PDTA114E_SERIES v.8
PDTA114E_SERIES v.8	20040802	Product specification	-	PDTA114E_SERIES v.7
PDTA114E_SERIES v.7	20030410	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTA114E_SER

PDTA114E series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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PDTA114E series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.